



IRW

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant : Tse-Yao HUANG et al. Confirmation No: 4935  
Appl. No. : 10/653,882  
Filed : September 4, 2003  
Title : ETCHING METHOD AND RECIPE FOR FORMING  
HIGH ASPECT RATIO CONTACT HOLE

TC/A.U. : 2812  
Examiner : Olivia T. Luk

Docket No.: : HUAN3211/REF  
Customer No: : 23364

**AMENDMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of May 13, 2005, in connection with the above-identified application. This response is timely filed.

Please amend the application as follows:

Amendments to the specification begin on page 2 of this paper.

Amendments to the claims are reflected in the listing of claims which begins on page 3 of this paper.

Remarks begin on page 5 of this paper.